

Comment on “Voltage-Current Characteristics of the Two-Dimensional Gauge Glass Model”

Li [1] has computed the current-voltage characteristics (CVC) of a disordered two-dimensional (2D) Josephson-junction array and claimed that his data, presented in Fig.1 of Ref.[1], gives evidence for a finite-temperature phase transition in the 2D gauge-glass model in contradiction to the result of equilibrium simulations [2]. His conclusion is based on the observation that the CVC is nonlinear for temperatures $T < 0.2$. I have computed a CVC of a resistively shunted **single** Josephson junction in the same current and temperature range as Li [1] did for the array, using the equation

$$V/RI_c = T/\pi [2/\pi \int_0^{\pi/2} d\phi \cosh(2\phi I/I_c T) I_0(2\cos\phi/T)]^{-1} \sinh(\pi I/I_c T), \quad (1)$$

which is an analytical solution for the Langevin equation for resistively shunted Josephson junction [3]. Here V is the voltage I is the current, R is the shunt resistance, I_c is the critical current of the junction, and I_0 is zero order modified Bessel function. Results are presented in Fig.1. In Fig.1(a) part of the data of Fig.1(b) is plotted, corresponding to the region of resistivities and currents studied by Li [1]. One can easily notice a remarkable resemblance between Fig.1(a) and Fig.1 of Ref.[1]: the CVC for $T < 0.2$ is also nonlinear for a single junction. One can even collapse the data of Fig.1(a) on a “scaling” curve (Fig.2), which is just as well as Li’s (see Fig.2 of Ref.[1]). Is the single junction in a “gauge-glass” state? However, it is sufficient to look at Fig.1(b) to understand that the nonlinear CVC is just a finite-current effect. I expect the same thing to happen for the 2D gauge glass, but to check this numerically would require enormous computation time, as there is no an analytical solution for Langevin equation for system of many junctions. Fig.1 of Ref.[1] is no more evidence of a finite-temperature 2D gauge-glass transition of a disordered Josephson-junction array than Fig.1(a) is evidence of this “transition” for a single junction.

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References

- [1] Y.H.Li, Phys. Rev. Lett. **69**,1819 (1992).
- [2] M.P.A. Fisher, T.A. Tokuyasu, and A.P. Young, Phys. Rev. Lett. **66**, 2931 (1991).
- [3] K.K. Likharev, Dynamics of Josephson Junctions and Circuits (Gordon and Breach, New York, 1986), chap 4.4. Eq.1 of the present comment is equation 4.60(b) of this reference.

Figure 1: Resistivity V/RI vs current I/I_c of a single Josephson junction at $T=0.05, 0.1, 0.2, 0.3, 0.4$ (from bottom). (a) contains a part of the data of (b), corresponding to the region of currents and resistivities studied by Li[1] and is remarkably similar to Fig.1 of Ref[1].

Figure 2: $V/RI|T - T_g|^{-z\mu}$ vs $I/I_c(|T - T_g|^{-\mu}/T)$ using the data as in Fig.1a. I used the same values of critical exponents ($\mu = 2.2, z = 2.2$) and transition temperature ($T_g = 0.15$) as Li (see Fig.2 of Ref.[1]).





